

急出货

High-current gain Power Transistor (60V, 3A)

2SD2318/2SD1944

●Features

- 1) High DC current gain.
- 2) Low saturation voltage, typically $V_{CE(sat)} = 0.5V$ at $I_C / I_B = 2A / 0.5A$.
- 3) Complements the 2SB1639.

●Packaging specifications and hFE

Type	2SD2318	2SD1944
Package	CPT3	TO-220FP
hFE	UV	HJK
Code	TL	—
Basic ordering unit (pieces)	2500	500

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	80	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	3	A
		4.5	A (Pulse) *
Collector power dissipation	Pc	1	W
		15	W (Tc=25°C)
		2	W
		30	W (Tc=28°C)
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

* Single pulse Pw=100ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	80	—	—	V	$I_C = 50 \mu A$
Collector-emitter breakdown voltage	BV_{CEO}	60	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	6	—	—	V	$I_E = 50 \mu A$
Collector cutoff current	I_{CBO}	—	—	100	μA	$V_{CB} = 80V$
Emitter cutoff current	I_{EBO}	—	—	100	μA	$V_{EB} = 6V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C / I_E = 2A / 0.05A$
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C / I_E = 2A / 0.05A$
DC current transfer ratio	hFE	2SD2318	560	1800	—	$V_{CE} / I_C = 4V / 0.5A$
		2SD1944	400	2000	—	
Transition frequency	f_T	—	50	—	MHz	$V_{CE} = 5V, I_E = -0.2A, f = 10MHz$
Output capacitance	C_{ob}	—	60	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

* Measured using pulse current.

(96-244-D302)

